



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03B Plastic-Encapsulate Diode

DS715NND03

Schottky barrier diode

DESCRIPTION

Epitaxial planar type Silicon diode

FEATURES:

Extra small power mold type.

Low VF

High reliability

APPLICATION

General rectification

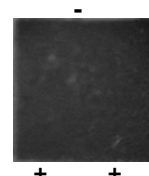
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

WBFBP-03B

(1.2×1.2×0.5)

unit: mm

TOP



1. ANODE

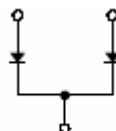
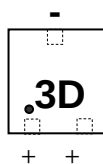
2. ANODE

3. CATHODE

BACK



MARKING: 3D



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25 °C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Maximum (peak) forward current	I _{FM}	200	mA
Average forward current	I _O	30	mA
Power dissipation	P _D	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse voltage leakage current	I _R	V _R =30V		0.5	μA
Forward voltage	V _F	I _F =1mA		0.37	V

Typical Characteristics

DS715NND03

